FORM PTO-1449 (Equivalent)

U.S. Department of Commerce Patent and Trademark Office U.S. Application Serial No. 09/991,166

Atty. Docket No. AM-5630.P1

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use several sheets if necessary)

Chentsau Ying et al. Applicants

November 16, 2001 Filing Date

<u>Unknown</u> Group



U. S. PATENT DOCUMENTS						
Examiner Initial	Document Number	Issue Date	Name	Class	Subclass	Filing Date If Appropriate
LV	5,811,356	09/22/98	Murugesh et al.	438	711	
	5,824,375	10/20/98	Gupta	427	569	
	6,020,035	02/01/00	Gupta et al.	427	534	
 	6,103,055	08/15/00	Maher et al.	156	345	
	6,121,161	09/19/00	Rossman et al.	438	783	
LV	6,143,078	11/07/00	Ishikawa et al.	118	715	
A		, 	FOREIGN PATENT DO	OCUMENTS		
Examiner	Danmark					· · · · · · · · · · · · · · · · · · ·
Initial	Document Number	Publication <u>Date</u>	Name	Class	Subclass	Translation If Appropriate
LV	EP 0892083	01/20/99	Qiao et al.	C23C	16/44	

Examiner

Date Considered

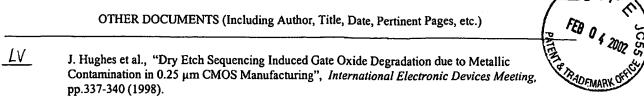
LAN VINH

11/18/04

Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Provided by the Applicant.

^{**} Cited in the specification by Applicant.



K. K. Singh et al., "Residual CF_x Radicals From Periodic Dry Cleans of Ar⁺ Sputter Etch Chember: Causes and Process Consequences", *Electrochemical Society Proceedings*, Vol. 31, pp.182-189 (1997).

S. Tehrani et al., "Progress and Outlook for MRAM Technology", IEEE Transactions on Magnetics, Vol. 35, No. 5, pp.2814-2819. (Sept 1999).

Examiner Date Considered

LAN VINA 11/18/02

Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

- * Provided by the Applicant.
- ** Cited in the specification by Applicant.